

Libre Silicon process specification

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Abstract

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This is the specification of the free silicon manufacturing standard for manufacturing the LibreSilicon standard logic cells¹ and related free technology nodes from the LibreSilicon project.

¹<https://github.com/chipforge/StdCellLib>

Contents

1	CMOS in a nutshell	4
2	Physics	6
2.1	Infusion	6
3	Process	7
3.1	Initial cleaning	8
3.1.1	Sulfuric Cleaning	8
3.1.2	HF dip	8
3.2	Well	9
3.2.1	Dioxide layer	9
3.2.2	Patterning	9
3.2.3	Etching	10
3.2.4	Cleaning	10
3.2.5	Predeposition	10
3.2.6	Sacrificial oxide	10
3.2.7	Infusion	11
3.2.8	Oxide removal	11
3.3	Channel stop	12
3.3.1	Dioxide layer	12
3.3.2	Nitride layer	12
3.3.3	Patterning	12
3.3.4	Etching	13
3.3.5	Cleaning	13
3.3.6	Predeposition	13
3.4	Field oxide	13
3.4.1	Thick oxide layer	13
3.4.2	Infusion	14
3.4.3	Patterning	14
3.4.4	Etching	14
3.5	Active	15
3.5.1	Gate oxide growth	15
3.5.2	Polysilicon growth	15
3.5.3	Patterning	15
3.5.4	Etching	16
3.5.5	Cleaning	16
3.6	p+ Implant	17
3.6.1	Dioxide layer	17
3.6.2	Patterning	17
3.6.3	Etching	17
3.6.4	Cleaning	18
3.6.5	Predeposition	18
3.6.6	Sacrificial oxide	18
3.6.7	Infusion	18
3.7	n+ Implant	19
3.7.1	Patterning	19
3.7.2	Etching	19
3.7.3	Cleaning	19

3.7.4	Predeposition	20
3.7.5	Sacrificial oxide	20
3.7.6	Infusion	20

1 CMOS in a nutshell

This basic initial project is dedicated to the CMOS Technology only and for this reason two types of metal-oxide-semiconductor field-effect transistors (MOSFET) are required.

Historically, the first chips with MOSFETs on the mass market were p-channel MOSFETs in enhancement-mode.

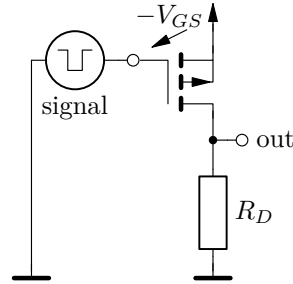
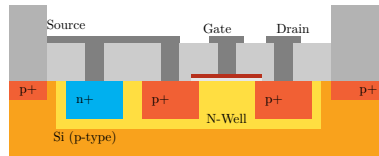


Figure 1: enhancement-mode PMOS transistor use-case

The sectional view of a PMOS transistor in silicon is being shown below



Historically later, faster chips with MOSFETs on the mass market were marked as n-channel MOSFETs in enhancement mode also.

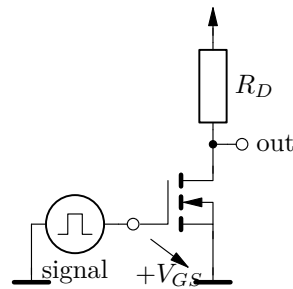
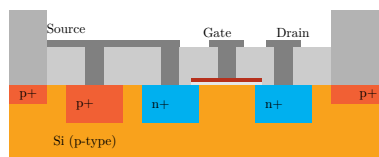


Figure 2: enhancement-mode NMOS transistor use-case

The sectional view of a NMOS transistor in silicon is being shown here also.



Both technologies, the older NMOS as the newer PMOS, have the same disadvantage. Every time, the transistor is switched on, the current between Drain and Source of the transistor is limited by the Resistor on Drain only. Higher currents here meaning also higher power consumption for the chip where the transistors are integrated also. If the transistors are switched off, now currents flows between Drain and Source anymore, the power consumption of the chip also goes low. Et voilà, the US-Patent with Number 3356858² changed the world and combines both technologies to the new complementary metal-oxide-semiconductor (CMOS) technology. Instead of every transistor is working against a weak resistor, the transistor works against a complementary switched-off transistor. With the Eyes of our antecessor CMOS doubles the transistor count, but contemporary chips all are build in CMOS.

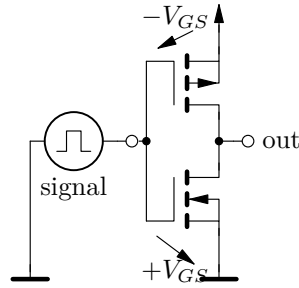
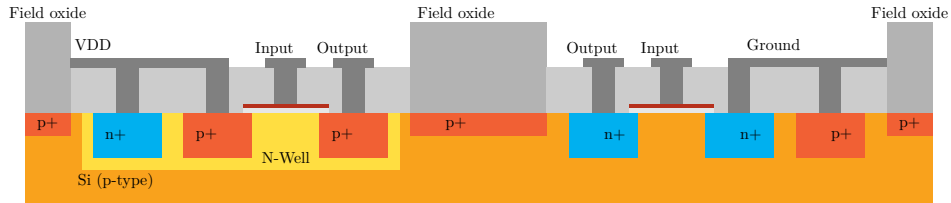


Figure 3: complementary PMOS and NMOS transistor couple use-case

Below the sectional view of the inverter circuitry can be seen. For the run through of this process we will use this cross section diagram as reference.



²<https://www.google.com/patents/US3356858>

2 Physics

2.1 Infusion

The redistribution process depends on the ratio of the solubility of the doping material in silicon and SiO_2 . At the Si/ SiO_2 interface the dopants are redistributed by segregation until the ratio of their concentration at the interface is the same as the ratio of their solubility in both materials. The ratio of dopant solubility is expressed by the segregation coefficient m which is

$$m = \frac{\text{solubility in silicon}}{\text{solubility in SiO}_2} \quad (1)$$

As listed in [Table 1](#) below there are dopant species which solubilize better in SiO_2 than in silicon ($m < 1$) and species which have a reversed behavior ($m > 1$). In case of $m < 1$, as for Boron, the dopant concentration is enhanced at the SiO_2 side, whereas beneath the interface, there is a dopant depletion at the silicon surface. For reversed solubility ratios ($m > 1$, like Phosphorus), only few dopant atoms penetrate the interface. In order to obtain the by m determined concentration ratio at the interface, dopant atoms from deeper silicon zones diffuse back to the surface zone. Therefore, the dopant concentration at the silicon surface is enhanced, as illustrated in [Figure 4b](#). In [Figure 4](#) C_c denotes the dopant concentration in the silicon surface zone before oxidation. x is the distance from the silicon surface.

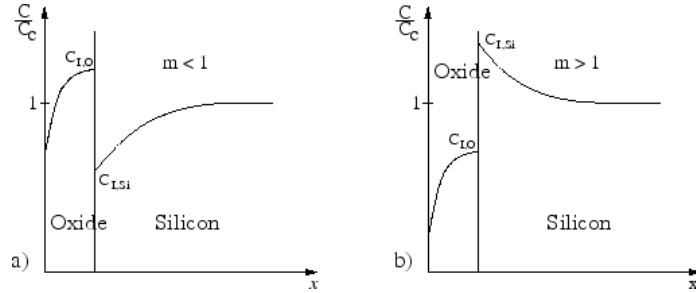


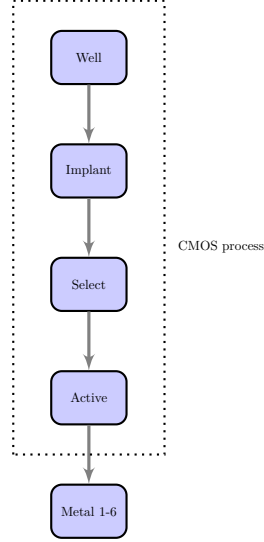
Figure 4: Schematic illustration of dopant redistribution

Dopant species	Boron	Phosphor	Antimon	Arsen	Gallium
m	0.1-0.3	10	10	10	20

Table 1: Segregation coefficients m for important dopant species in silicon

3 Process

Below the general flow chart of the overall process flow can be seen. These process steps will be discussed within the following sections.



The four starting overall process steps are part of an overall active part of the technology, while the final metal (respectively contact) layers will be used for making a contact between the logic gates and macro cells and making them available to the exterior world. For this process p-substrate is the required basic substrate, but forks and modifications will be very well possible based on a Graphene substrate or alike, still under the LSPL. The decision to use an n-well approach is based largely on the compatibility with the existing nMOS process. The starting material is a p-type, <100> oriented silicon with a doping concentration of $\approx 9 \times 10^{14} cm^{-3}$.

3.1 Initial cleaning

In order to remove the initial naturally grown silicon dioxide from the wafer, acid is being applied to the wafer which leads to a pure silicon substrate wafer as in the process illustration shown below.



This needs to be done because the naturally grown initially existing silicon oxide is not pure and may contain contamination which may render the final product unusable.

3.1.1 Sulfuric Cleaning

The sulfuric acid mixture, $H_2SO_4 + H_2O_2$ is being applied to the wafer for 10 minutes at a temperature of 120 °C.

3.1.2 HF dip

After the sulfuric cleaning a HF (HF:H₂O , 1:50) dip is being performed for one minute.

Hydrofluoric acid (HF) is used to remove native silicon dioxide from wafers. Since it acts quickly, one needs to only expose the wafer for a short time ("dip"). After that the wafer needs to be dried and quickly processed further before new uncontrolled natural oxide can build up on the wafer through the contact with air.

3.2 Well

In order to build CMOS (Complementary metal–oxide–semiconductor/P and N MOS) on the same substrate an n-well is required for building the complementary P-channel transistor for a n-p-channel logic circuitry as shown above in the example section. The n-well will serve us as an island of n-doped substrate within the p-doped basis substrate. The cross section as well as the top view of the targeted geometry are shown below.



3.2.1 Dioxide layer

In order to selectively inject charge carrying atoms into the crystalline structure a protective dioxide (SiO_2) layer needs to be grown on top of a p-type substrate.



The industrial best practice is a layer of around ($500\text{nm} \approx 5000\text{\AA}$) thickness or more. For this purpose the wafer is being oxidized for at least 90 minutes at 1000°C using wet oxidation which results in a dioxide layer at least $500\text{nm} (\approx 5000\text{\AA})$ in thickness.

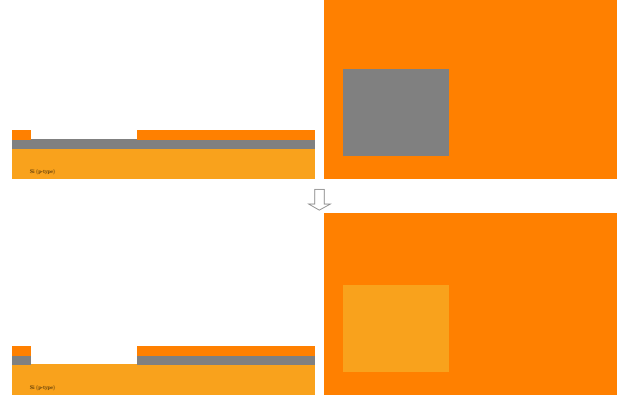
3.2.2 Patterning

The resist is being deposited using spin coating and then baked depending on the baking time for the specific resist. The layout for being exposed onto the resist is being extracted from the "nwell" layer within the GDS2 file.



The thickness of the resist layer and the backing duration will variate depending on the specific equipment for which this process will be implemented with.

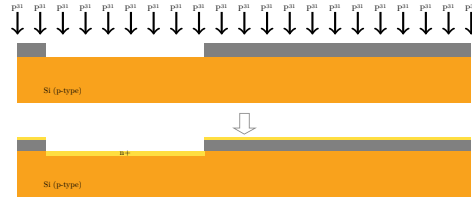
3.2.3 Etching



3.2.4 Cleaning



3.2.5 Predeposition



The n-well is implanted with a Phosphorus (P^{31}) dose of $2.5 \times 10^{12} cm^{-2}$ at an energy of 100 KeV. The n-well is then annealed.

3.2.6 Sacrificial oxide



The wafer is being oxidized for 32 minutes at 1000°C in order to achieve a cover silicon layer of 250nm thickness ($\approx 2500\text{\AA}$).

3.2.7 Infusion

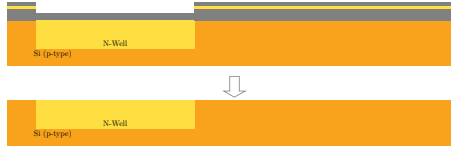
In order to drive the carrier atoms deeper into the crystalline structure the wafer needs to be driven in after predeposition.



In this step the wafer is driven-in for 960 minutes at 1150°C in an inert ambient.

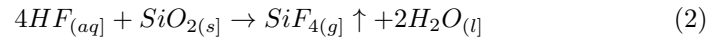
3.2.8 Oxide removal

We want an oxide free wafer with the n-well accessible for the further process steps.



We use hydrofluoric acid, because it doesn't etch silicon at all but is very aggressive towards SiO_2

For hydrofluoric acid in combination with SiO_2 the following reaction formula can be used



while with non oxidized silicon there is no reaction.

3.3 Channel stop

The channel-stop is material with the primary function to limit the spread of the channel area and to prevent the formation of parasitic channels. It is a highly doped p+ area. Its top view and cross section can be seen below.

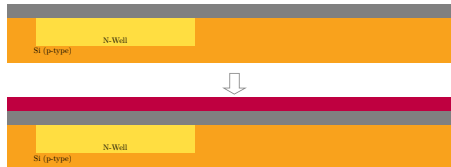


It surrounds all the active areas and covers all the non-active area. The channel-stop region is always accompanied by the field oxide layer and shares the same layout mask (just inverted) with it.

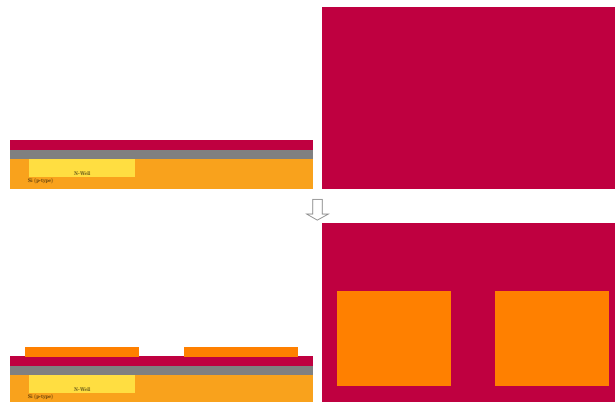
3.3.1 Dioxide layer



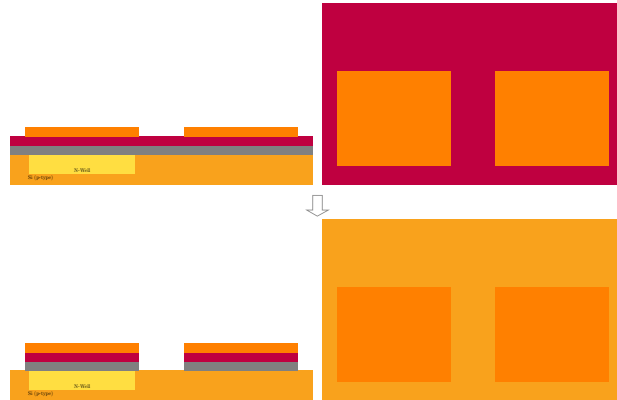
3.3.2 Nitride layer



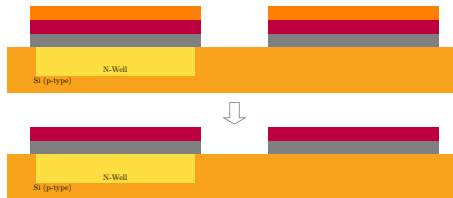
3.3.3 Patterning



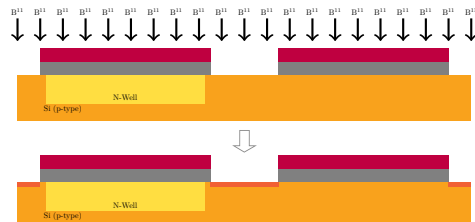
3.3.4 Etching



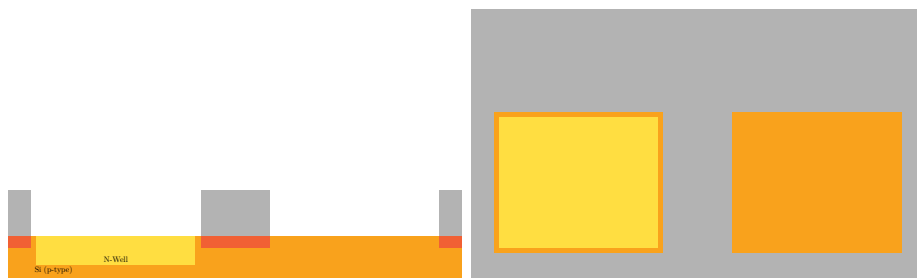
3.3.5 Cleaning



3.3.6 Predeposition

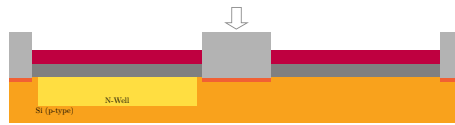


3.4 Field oxide

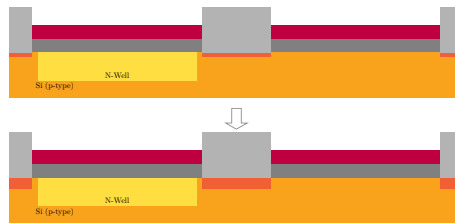


3.4.1 Thick oxide layer

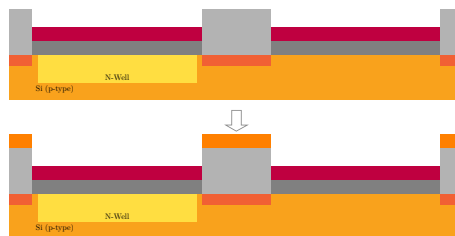




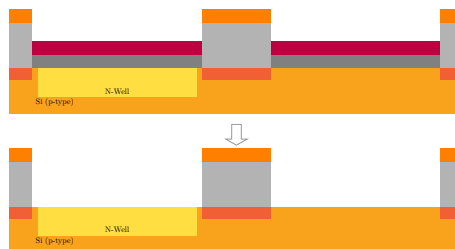
3.4.2 Infusion



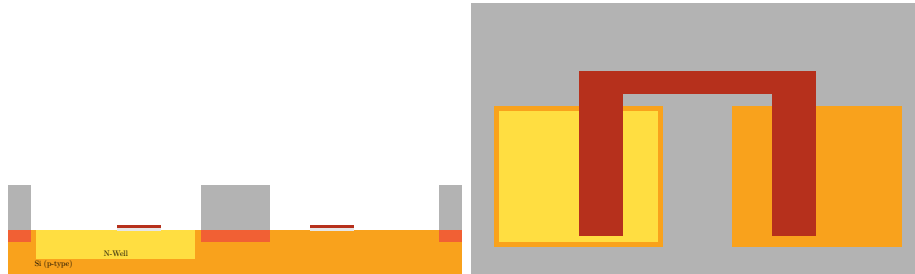
3.4.3 Patterning



3.4.4 Etching

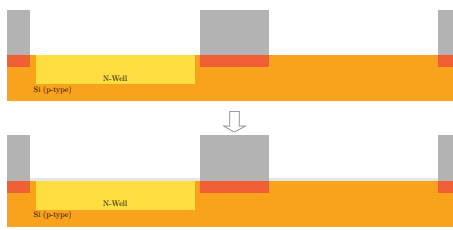


3.5 Active

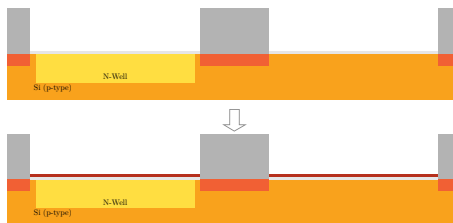


3.5.1 Gate oxide growth

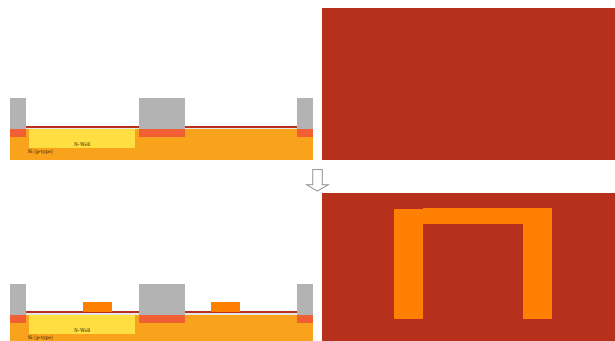
The thickness of the gate oxide depends the capacity (slew rate) of the transistor. The thinner the layer is, the steeper the edges of the CMOS circuitry will be, however also the threshold voltage will be reduced the thinner the gate oxide gets.



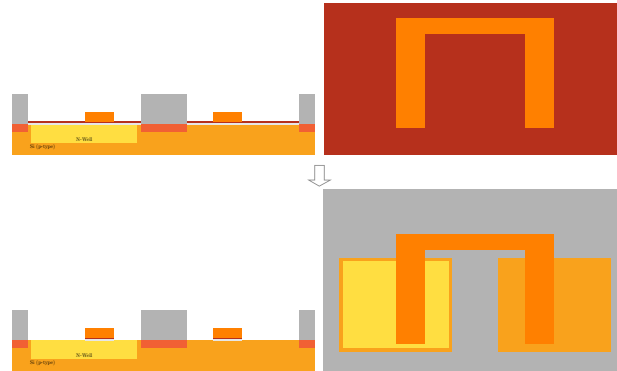
3.5.2 Polysilicon growth



3.5.3 Patterning

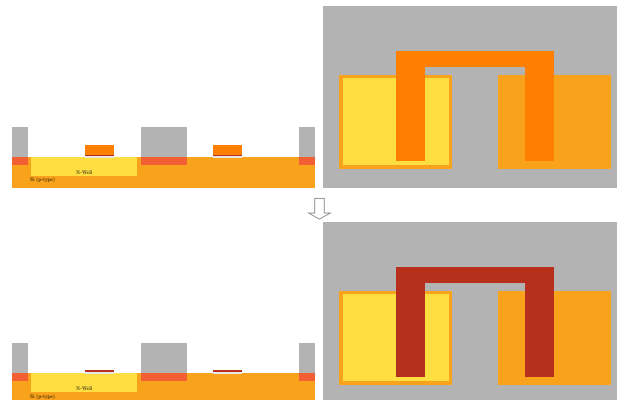


3.5.4 Etching

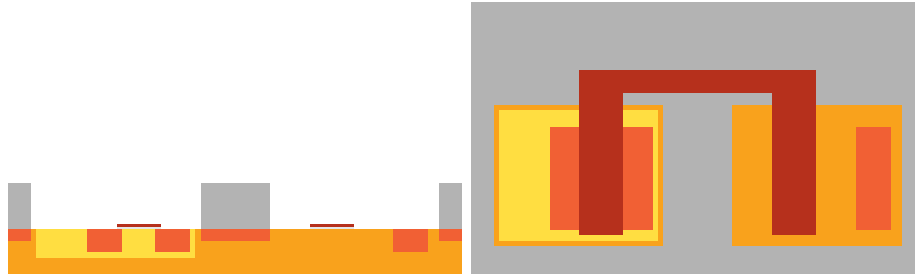


Because the exact shape of the gate contact is required for a reproducible property characterization of the transistor geometry, dry etching is being used for etching the poly-oxide layer stack.

3.5.5 Cleaning

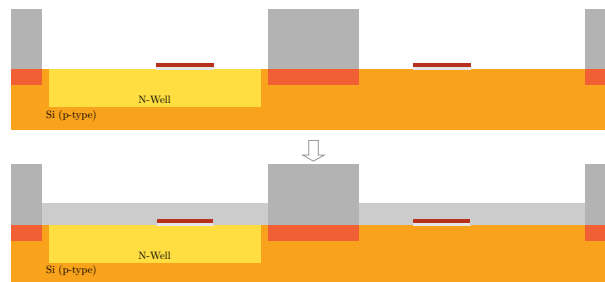


3.6 p+ Implant

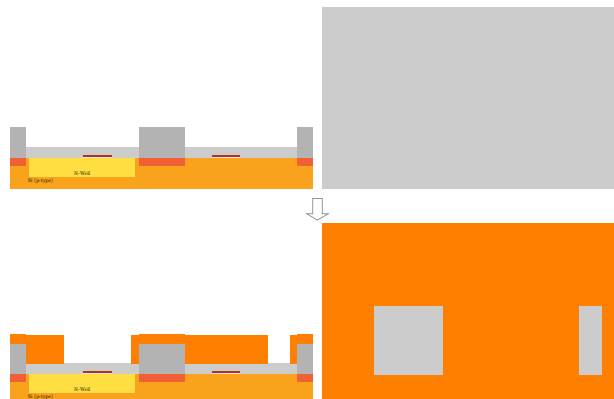


For the bulk of the NMOS transistors and for the source and drain of the PMOS transistors highly doped p+ areas are required. In this step we're going to build these.

3.6.1 Dioxide layer

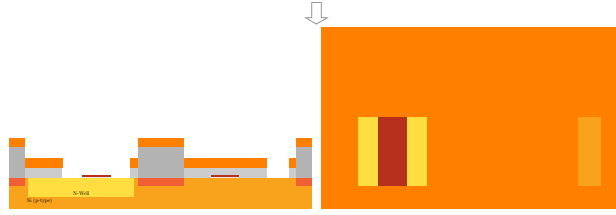


3.6.2 Patterning

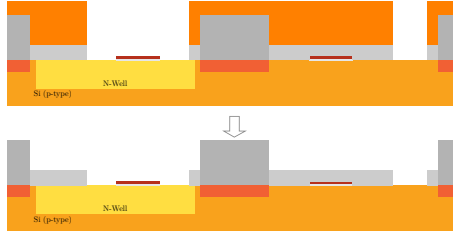


3.6.3 Etching

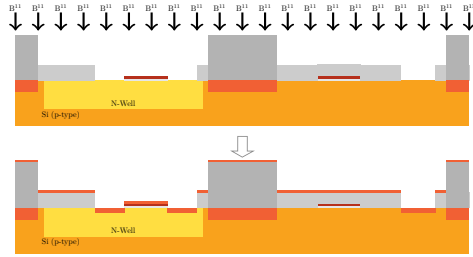




3.6.4 Cleaning

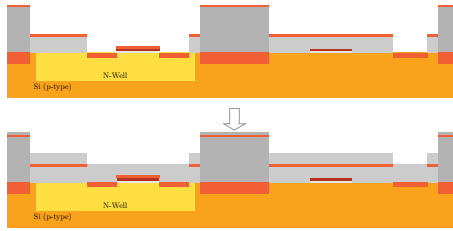


3.6.5 Predeposition

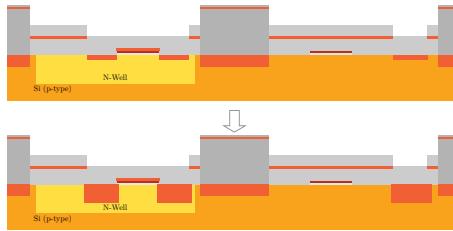


The p+ islands are implanted with a Boron (B^{11}) dose of $4 \times 10^{11} cm^{-2}$ at an energy of 35 KeV.

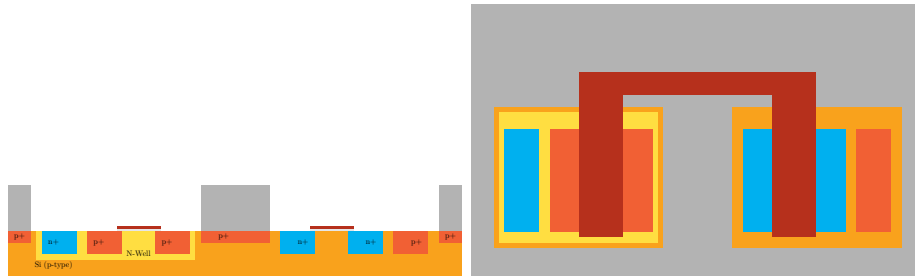
3.6.6 Sacrificial oxide



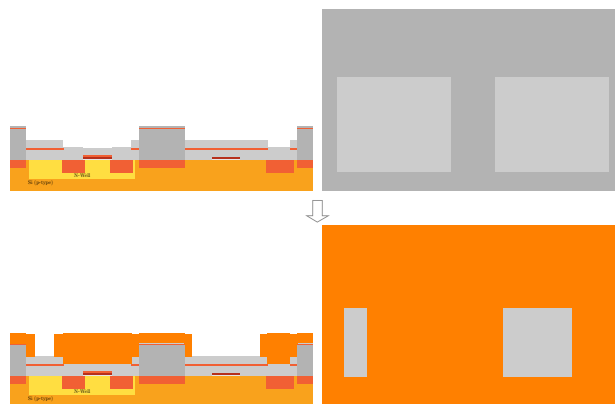
3.6.7 Infusion



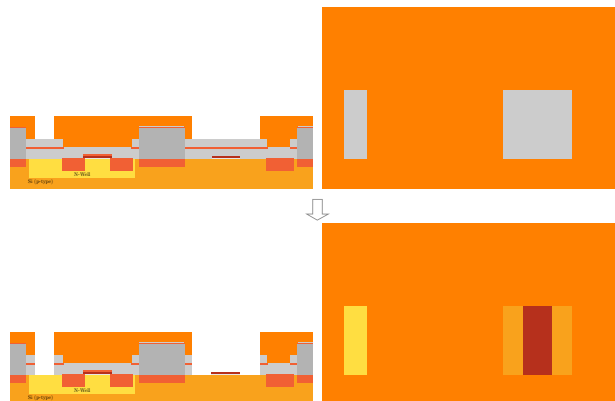
3.7 n+ Implant



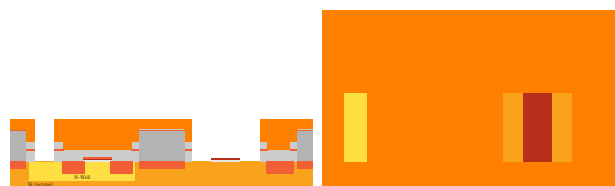
3.7.1 Patterning

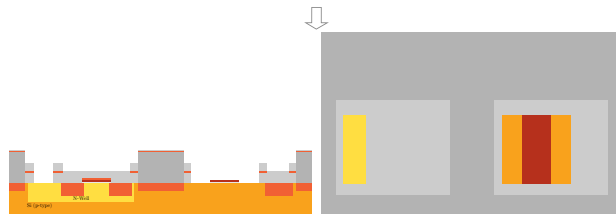


3.7.2 Etching

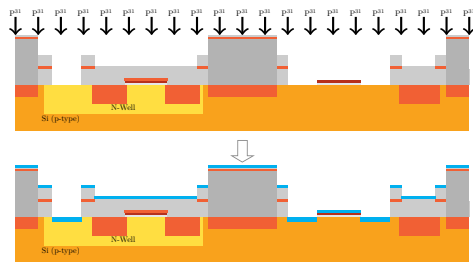


3.7.3 Cleaning

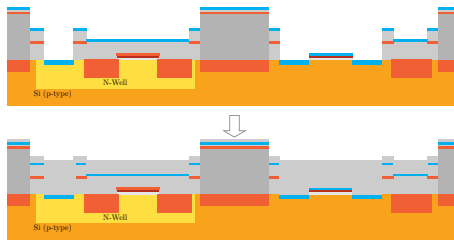




3.7.4 Predeposition



3.7.5 Sacrificial oxide



3.7.6 Infusion

